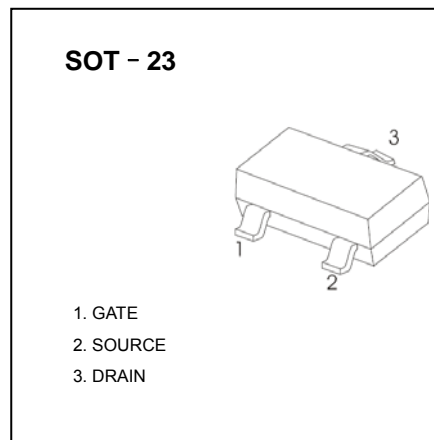
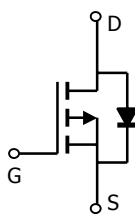


P-Channel Enhancement MOSFET

■ Features

- $V_{DS} (V) = -30V$
- $I_D = -4.1 A$
- $R_{DS(ON)} < 52m\ \Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 87m\ \Omega$ ($V_{GS} = -4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

| Parameter | Symbol | Rating | Unit |
|---|------------|--------------------|--------------|
| Drain-Source Voltage | V_{DS} | -30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current | I_D | $T_a = 25^\circ C$ | -4.1 |
| | | $T_a = 70^\circ C$ | -3.5 |
| Pulsed Drain Current | I_{DM} | -20 | A |
| Power Dissipation | P_D | $T_a = 25^\circ C$ | 1.4 |
| | | $T_a = 70^\circ C$ | 1 |
| Thermal Resistance.Junction- to-Ambient | R_{thJA} | $t \leq 10s$ | 90 |
| | | Steady State | 125 |
| Thermal Resistance.Junction- to-Lead | R_{thJL} | 60 | $^\circ C/W$ |
| Junction Temperature | T_J | 150 | $^\circ C$ |
| Storage Temperature Range | T_{stg} | -55 to 150 | |

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---------------------------------------|---------------------|--|--|-------|------|------|
| Drain-Source Breakdown Voltage | V _{DSS} | I _D =-250 μ A, V _{GS} =0V | -30 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =-24V, V _{GS} =0V | | | -1 | μ A |
| | | V _{DS} =-24V, V _{GS} =0V, T _J =55°C | | | -5 | |
| Gate-Body leakage current | I _{GSS} | V _{DS} =0V, V _{GS} =±20V | | | ±100 | nA |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} I _D =-250 μ A | -1 | -1.8 | -3 | V |
| Static Drain-Source On-Resistance | R _{DS(on)} | V _{GS} =-10V, I _D =-4.1A | | 40.5 | 52 | mΩ |
| | | V _{GS} =-10V, I _D =-4.A T _J =125°C | | 57 | 73 | |
| | | V _{GS} =-4.5V, I _D =-3A | | 64 | 87 | |
| On state drain current | I _{D(ON)} | V _{GS} =-4.5V, V _{DS} =-5V | -10 | | | A |
| Forward Transconductance | g _{FS} | V _{DS} =-5V, I _D =-4A | 5.5 | 8.2 | | S |
| Input Capacitance | C _{iss} | V _{GS} =0V, V _{DS} =-15V, f=1MHz | | 700 | | pF |
| Output Capacitance | C _{oss} | | | 120 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 75 | | |
| Gate resistance | R _g | | V _{GS} =0V, V _{DS} =0V, f=1MHz | | 10 | |
| Total Gate Charge | Q _g | V _{GS} =-4.5V, V _{DS} =-15V, I _D =-4A | | 14.3 | | nC |
| Gate Source Charge | Q _{gs} | | | 7 | | |
| Gate Drain Charge | Q _{gd} | | | 3.1 | | |
| Turn-On DelayTime | t _{d(on)} | V _{GS} =-10V, V _{DS} =-15V, R _L =3.6Ω, R _{GEN} =3Ω | | 8.6 | | ns |
| Turn-On Rise Time | t _r | | | 5 | | |
| Turn-Off DelayTime | t _{d(off)} | | | 28.2 | | |
| Turn-Off Fall Time | t _f | | | 13.5 | | |
| Body Diode Reverse Recovery Time | t _{rr} | | | 27 | | |
| Body Diode Reverse Recovery Charge | Q _{rr} | I _F =-4A, di/dt=100A/μ s | | 15 | | nC |
| Maximum Body-Diode Continuous Current | I _S | | | | -2.2 | A |
| Diode Forward Voltage | V _{SD} | I _S =-1A, V _{GS} =0V | | -0.77 | -1 | V |

■ Typical Characteristics

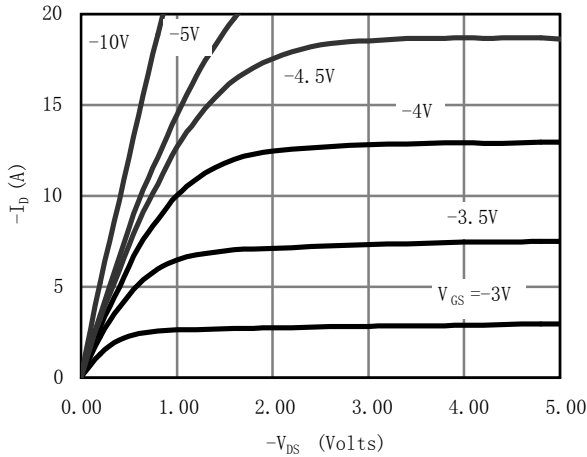


Figure 1: On-Region Characteristics

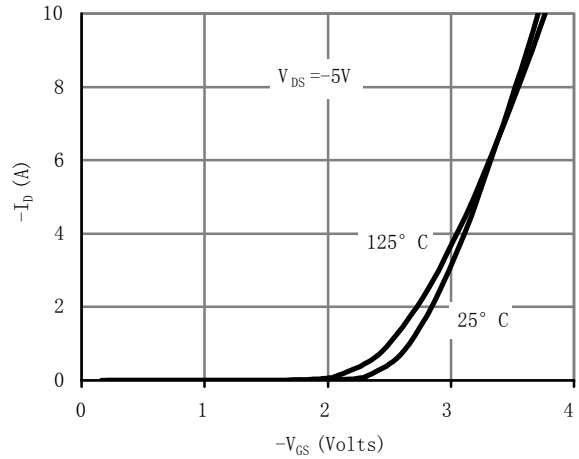


Figure 2: Transfer Characteristics

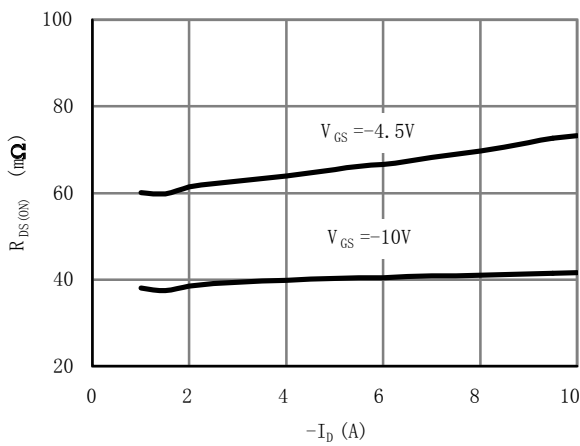


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

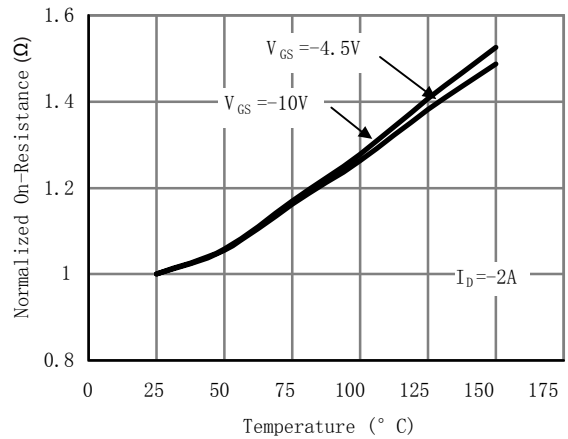


Figure 4: On-Resistance vs. Junction Temperature

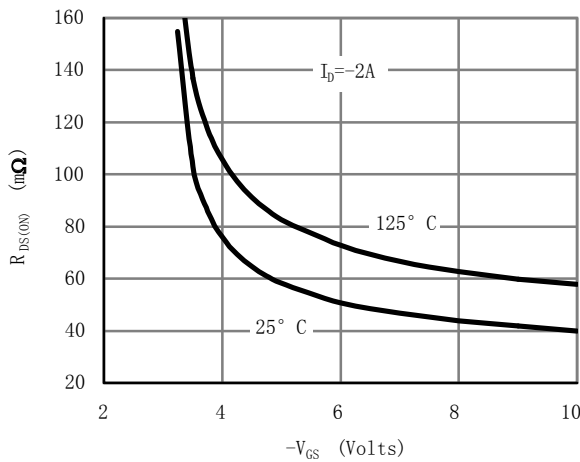


Figure 5: On-Resistance vs. Gate-Source Voltage

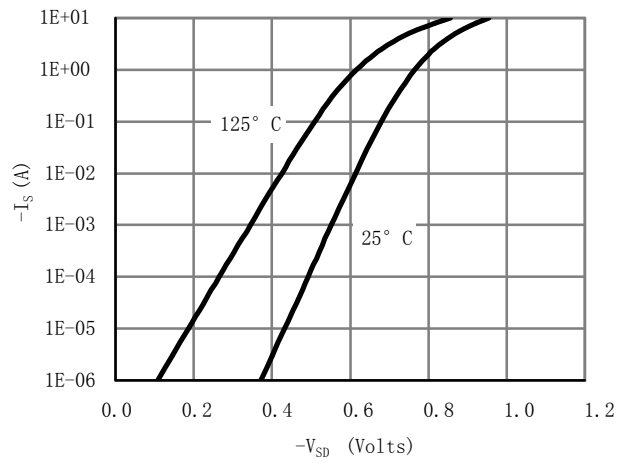


Figure 6: Body-Diode Characteristics

■ Typical Characteristics

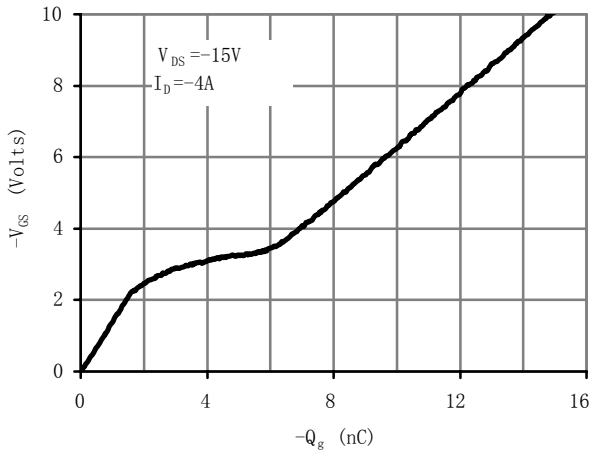


Figure 7: Gate-Charge Characteristics

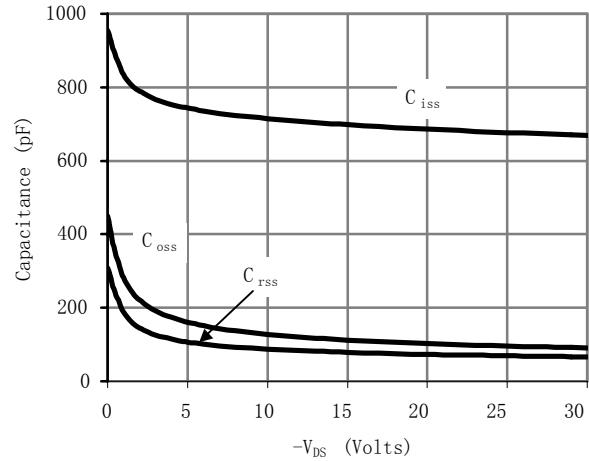


Figure 8: Capacitance Characteristics

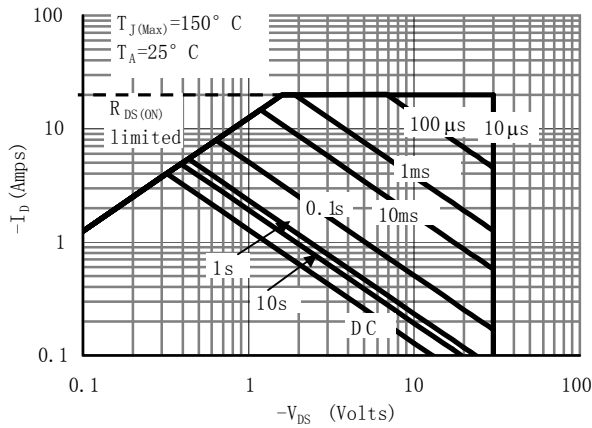


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

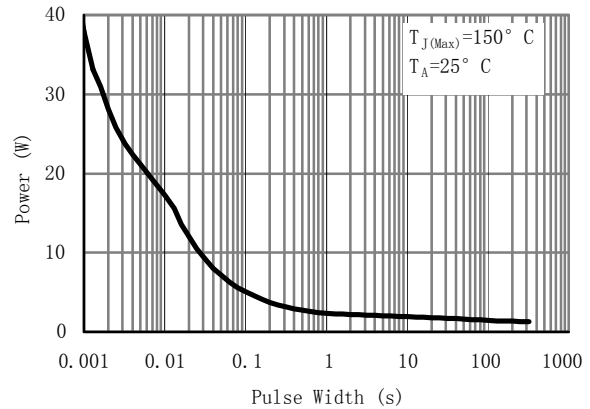


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

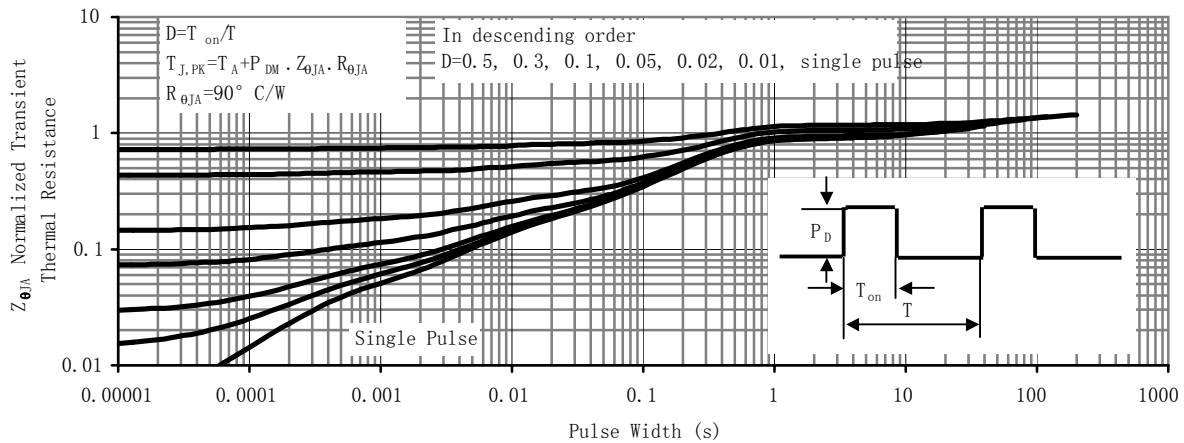


Figure 11: Normalized Maximum Transient Thermal Impedance